

B1 end

a ferroelectric thin film epitaxially grown on said perovskite oxide thin film.

5. (Amended) The multilayer thin film of claim 1, wherein said ferroelectric thin

B2

film comprises PZT.

7. (Amended) A process for preparing the multilayer thin film of claim 1,

comprising:

B3
forming a buffer layer including an oxide thin film of zirconium or of a rare earth element on an Si (100) substrate,

epitaxially growing a perovskite oxide thin film having a (100) or (001) orientation on said buffer layer, and

epitaxially growing a ferroelectric thin film on said perovskite oxide thin film.

Please add the following Claims 8 and 9:

8. (New) The multilayer thin film of claim 1, wherein said buffer layer comprises

B4
 ZrO_2 .

9. (New) The multilayer thin film of claim 1, wherein said buffer layer comprises

Y_2O_3 .

BASIS FOR THE AMENDMENT

The claims have been limited to the buffer layer including an oxide thin film of zirconium or a rare earth element, consistent with the disclosure at page 9, lines 11-13 and in the Example at page 20 of the specification.

REMARKS

Favorable reconsideration of this application is requested.

Claims 1-9 are in the case.